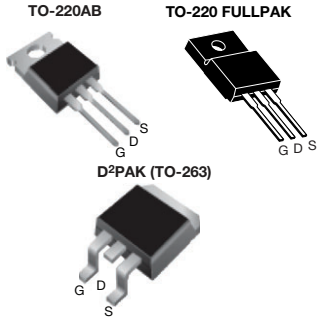
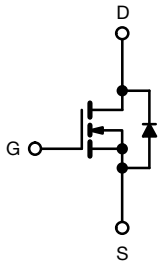
Power MOSFET





N-Channel MOSFET

FEATURES

- Low figure-of-merit R_{on} x Q_g
- 100 % avalanche tested
- Gate charge improved
- t_{rr}/Q_{rr} improved
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Available

RoHS* Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

PRODUCT SUMMARY		
V_{DS} (V) at T_J max.	560	
$R_{DS(on)}$ (Ω)	V_{GS} = 10 V	0.38
Q_g (Max.) (nC)	68	
Q_{gs} (nC)	17.6	
Q_{gd} (nC)	21.8	
Configuration	Single	

ORDERING INFORMATION			
Package	TO-220AB	D²PAK (TO-263)	TO-220 FULLPAK
Lead (Pb)-free	SiHP16N50C-E3	SiHB16N50C-E3	SiHF16N50C-E3
	-	SiHB16N50CTR-E3	-
	-	SiHB16N50CTL-E3	-
Lead (Pb)-free and halogen-free	SiHP16N50C-BE3	-	-

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V_{DS}	500	V
Gate-source voltage			V_{GS}	± 30	
Continuous drain current (T_J = 150 °C) [a]	V_{GS} at 10 V	T_C = 25 °C	I_D	16	A
		T_C = 100 °C		10	
Pulsed drain current [c]			I_{DM}	40	
Linear derating factor				2	W/°C
Single pulse avalanche energy [b]			E_{AS}	320	mJ
Maximum power dissipation	TO220-AB, D²PAK (TO-263)		P_D	250	W
	TO-220 FULLPAK			38	
Operating junction and storage temperature range			T_J, T_{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) [d]	For 10 s			300	

Notes

a. Limited by maximum junction temperature
b. V_{DD} = 50 V, starting T_J = 25 °C, L = 2.5 mH, R_g = 25 Ω, I_{AS} = 16 A
c. Repetitive rating; pulse width limited by maximum junction temperature
d. 1.6 mm from case

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TO220-AB D²PAK (TO-263)**	**TO-220 FULLPAK**	**UNIT**
Maximum junction-to-ambient	R_{thJA}	62	65	°C/W
Maximum junction-to-case (drain)	R_{thJC}	0.5	3.3	
Junction-to-ambient (PCB mount) [a]	R_{thJA}	40	-	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material)

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	500	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA	-	0.6	-	V/°C
Gate-source threshold voltage (N)	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	3.0	-	5.0	V
Gate-source leakage	I_{GSS}	V_{GS} = ± 30 V	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = 500 V, V_{GS} = 0 V	-	-	50	µA
		V_{DS} = 400 V, V_{GS} = 0 V, T_J = 125 °C	-	-	250	
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS} = 10 V; I_D = 8 A	-	0.31	0.38	Ω
Forward transconductance [a]	g_{fs}	V_{DS} = 50 V, I_D = 3 A	-	3	-	S
Dynamic						
Input capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1.0 MHz	-	1900	-	pF
Output capacitance	C_{oss}		-	230	-	
Reverse transfer capacitance	C_{rss}		-	24	-	
Total gate charge	Q_g	V_{GS} = 10 V; I_D = 16 A, V_{DS} = 400 V	-	45	68	nC
Gate-source charge	Q_{gs}		-	18	-	
Gate-drain charge	Q_{gd}		-	22	-	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 250 V, I_D = 16 A, R_g = 9.1 Ω, V_{GS} = 10 V	-	27	-	ns
Rise time	t_r		-	156	-	
Turn-off delay time	$t_{d(off)}$		-	29	-	
Fall time	t_f		-	31	-	
Gate input resistance	R_g	f = 1 MHz, open drain	-	1.6	-	Ω
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	16	A
Pulsed diode forward current	I_{SM}		-	-	30	
Body diode voltage	V_{SD}	T_J = 25 °C, I_S = 10 A, V_{GS} = 0 V	-	-	1.8	V
Body diode reverse recovery time	t_{rr}	T_J = 25 °C, I_F = I_S, dI/dt = 100 A/µs, V_R = 20 V	-	555	-	ns
Body diode reverse recovery charge	Q_{rr}		-	5.5	-	µC
Body diode reverse recovery current	I_{RRM}		-	18	-	A

Note

- The information shown here is a preliminary product proposal, not a commercial product data sheet. Vishay Siliconix is not committed to produce this or any similar product. This information should not be used for design purposes, nor construed as an offer to furnish or sell such products

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

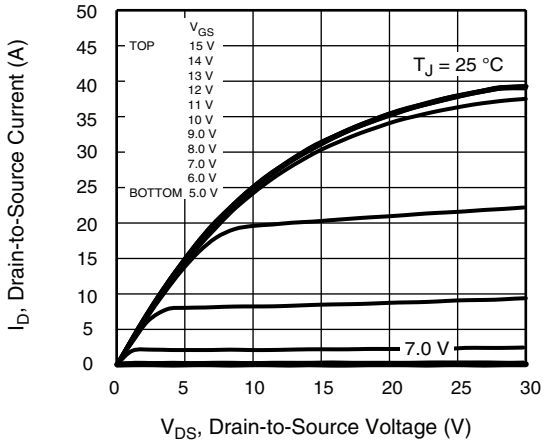


Fig. 1 - Typical Output Characteristics (TO-220)

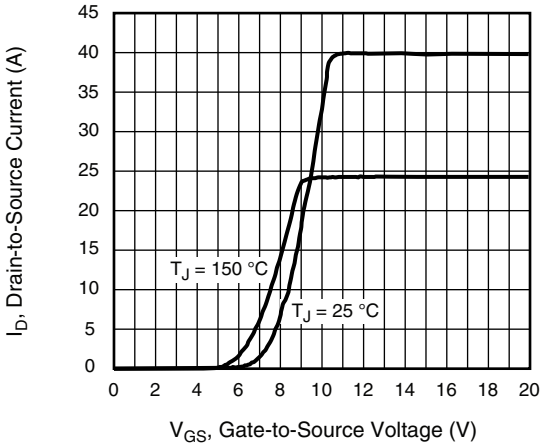


Fig. 3 - Typical Transfer Characteristics

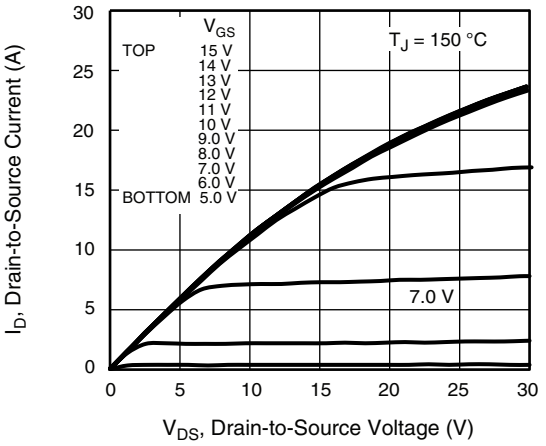


Fig. 2 - Typical Output Characteristics (TO-220)

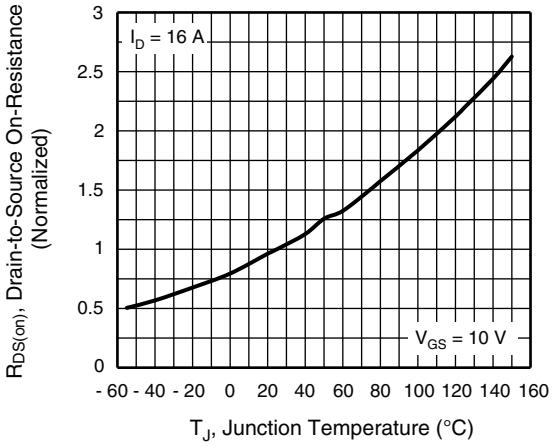


Fig. 4 - Normalized On-Resistance vs. Temperature

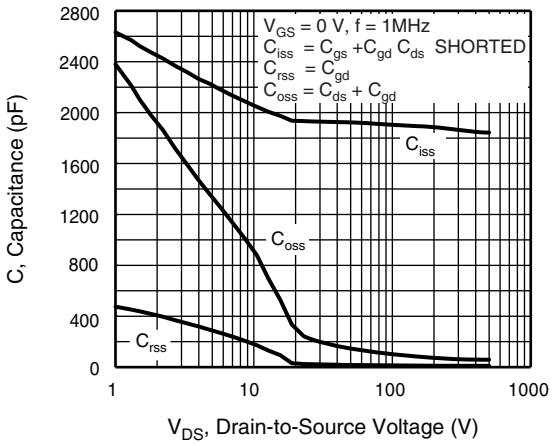


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

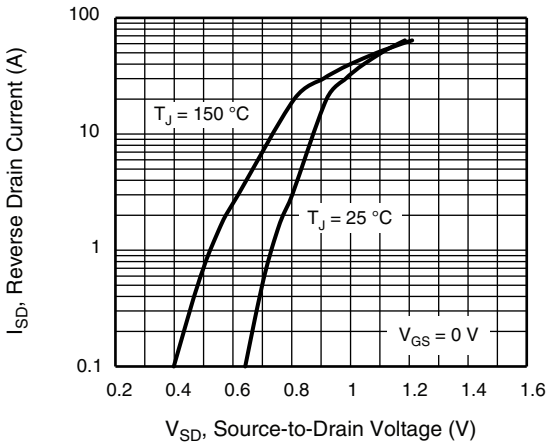


Fig. 7 - Typical Source-Drain Diode Forward Voltage

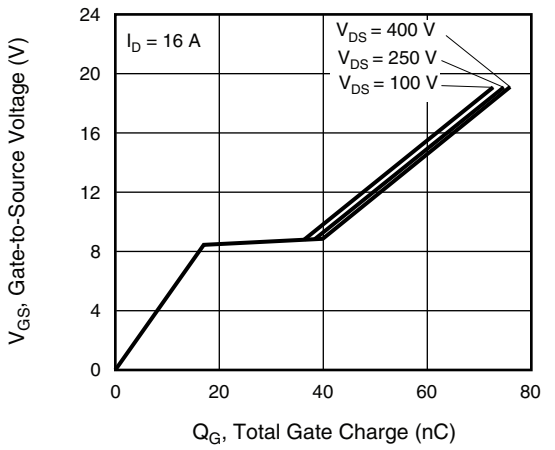


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

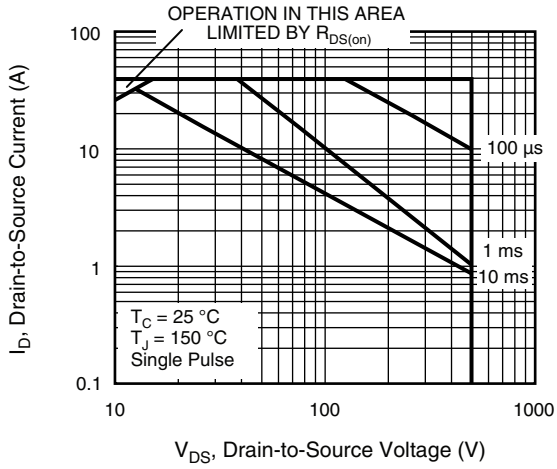


Fig. 1 - Maximum Safe Operating Area (TO-220AB, D^2PAK)

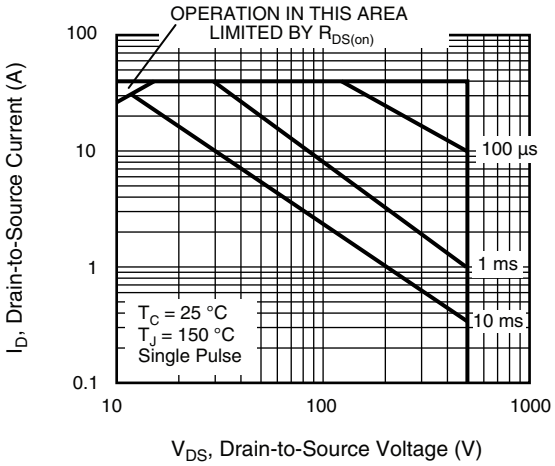


Fig. 2 - Maximum Safe Operating Area (TO-220 FULLPAK)

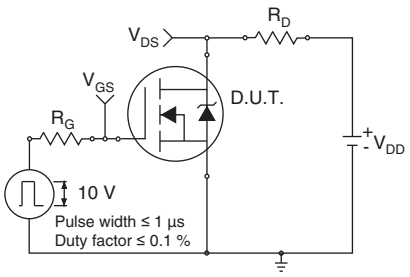


Fig. 10a - Switching Time Test Circuit

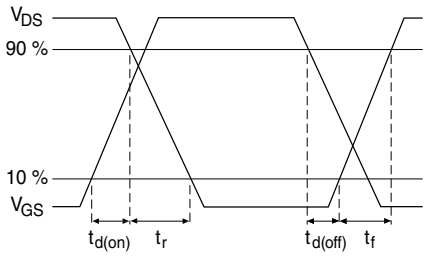


Fig. 10b - Switching Time Waveforms

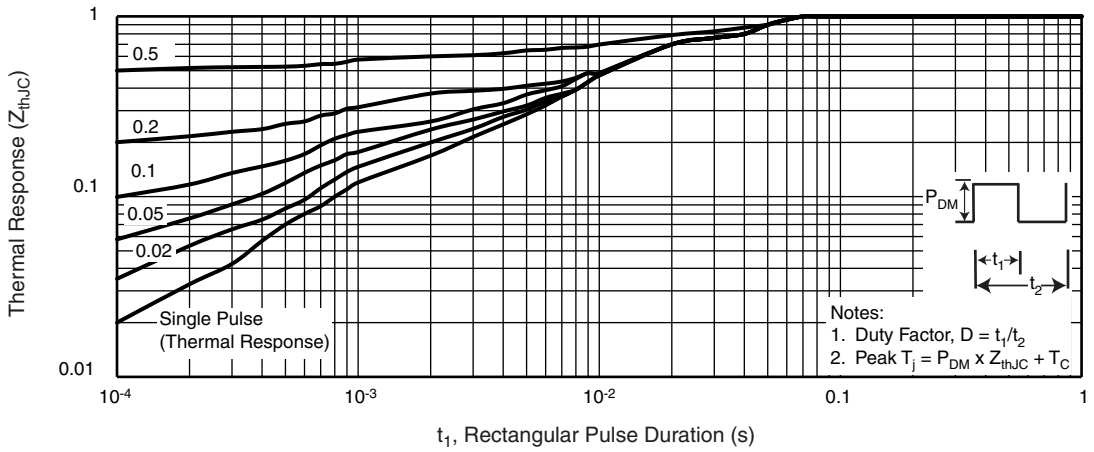


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220AB, D^2PAK)

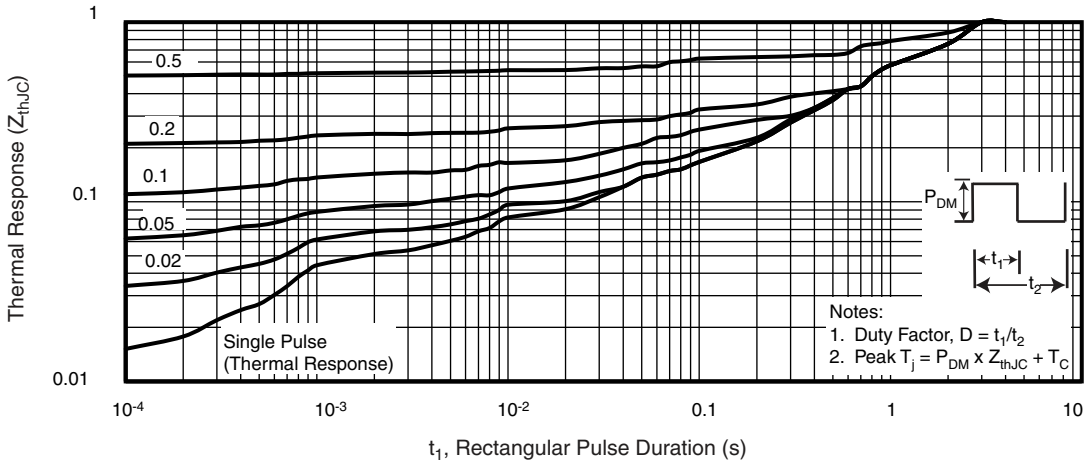


Fig. 3 - Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220 FULLPAK)

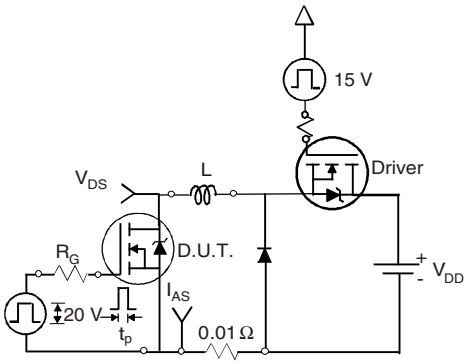


Fig. 13a - Unclamped Inductive Test Circuit

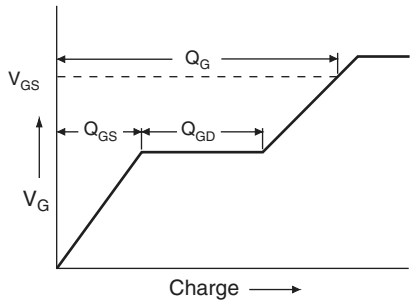


Fig. 14a - Basic Gate Charge Waveform

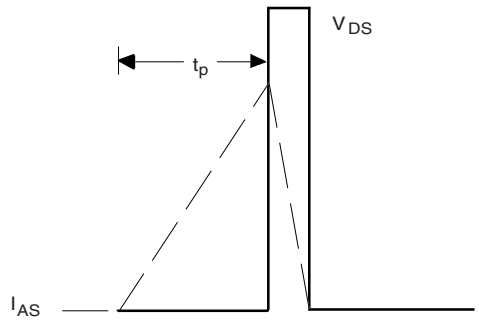


Fig. 13b - Unclamped Inductive Waveforms

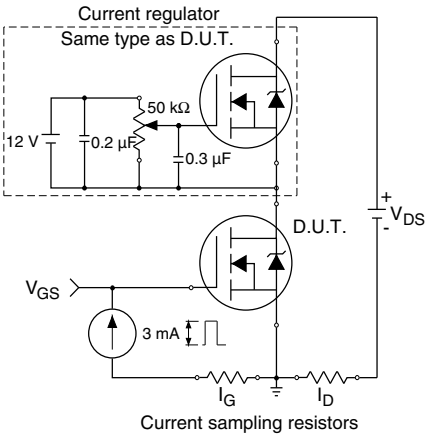
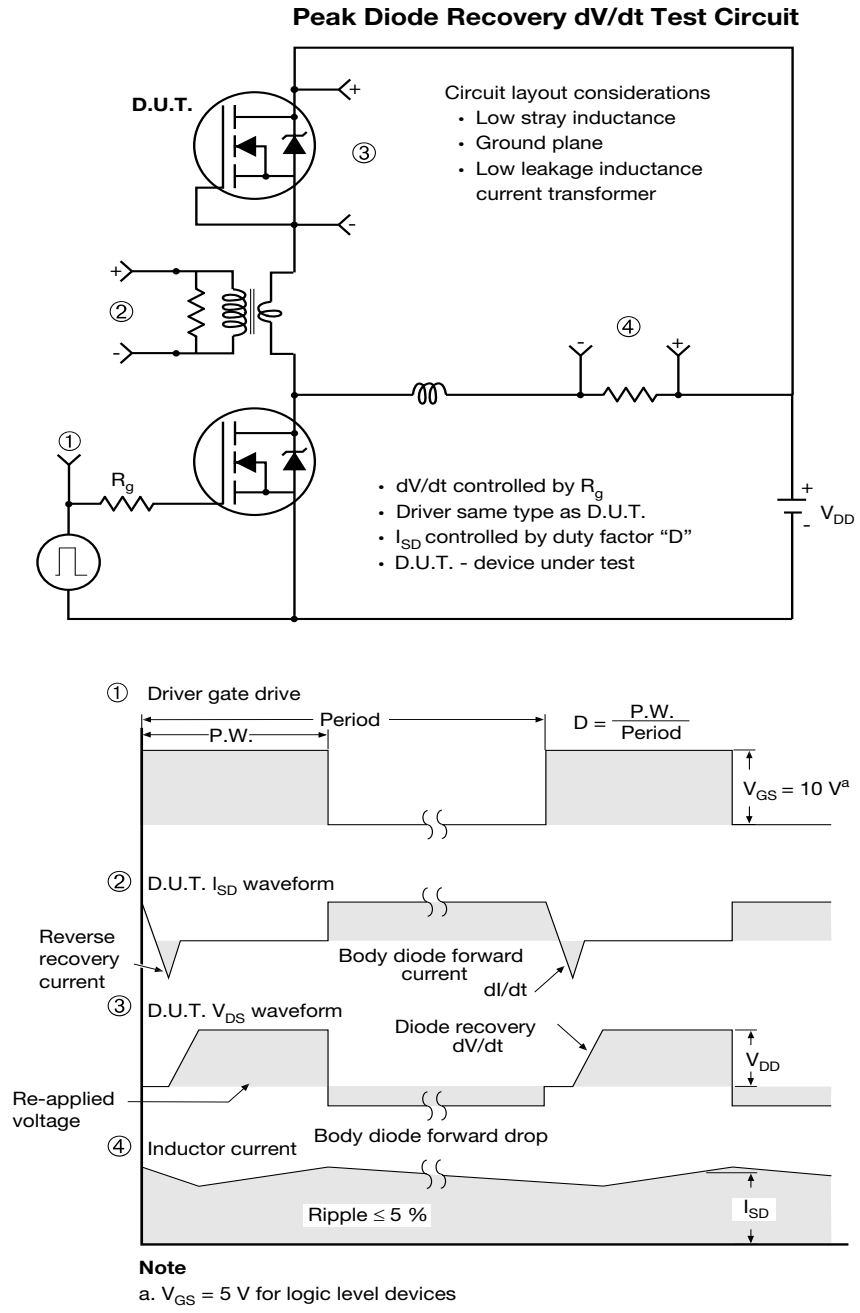


Fig. 14b - Gate Charge Test Circuit

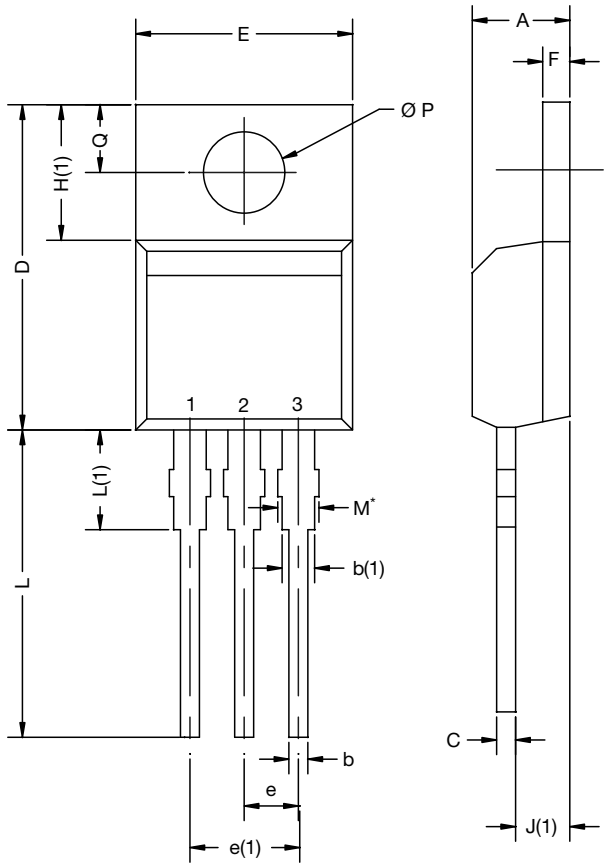


Note

a. V_{GS} = 5 V for logic level devices

Fig. 15 - For N-Channel

TO-220-1



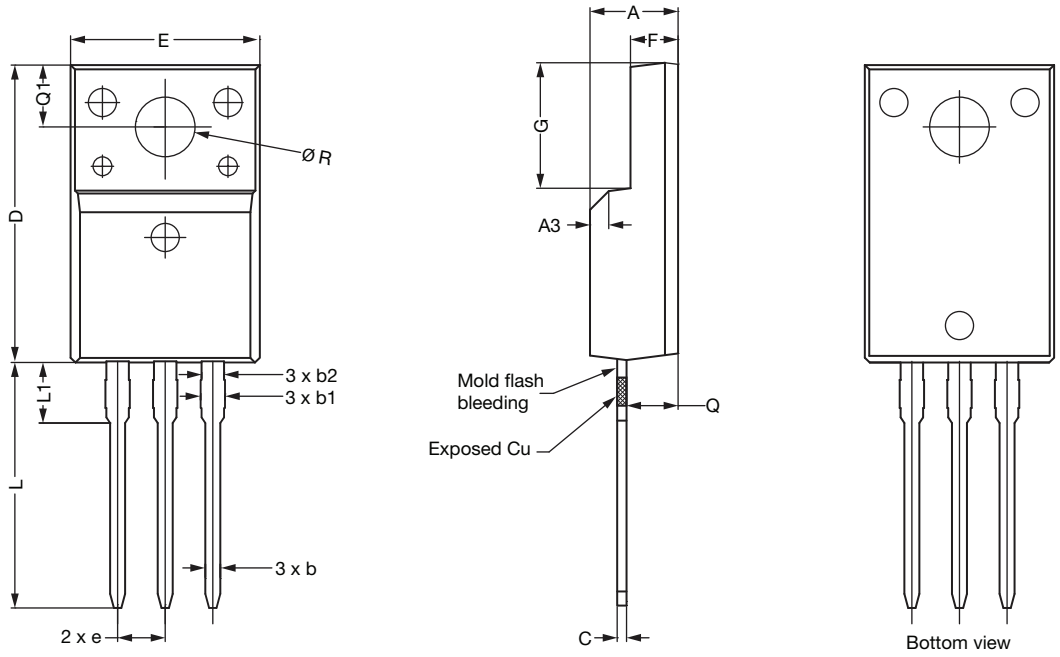
DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
Ø P	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118
ECN: E21-0621-Rev. D, 04-Nov-2021 DWG: 6031				

Note

- M* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM

TO-220 FULLPAK (High Voltage)

OPTION 1: FACILITY CODE = 9

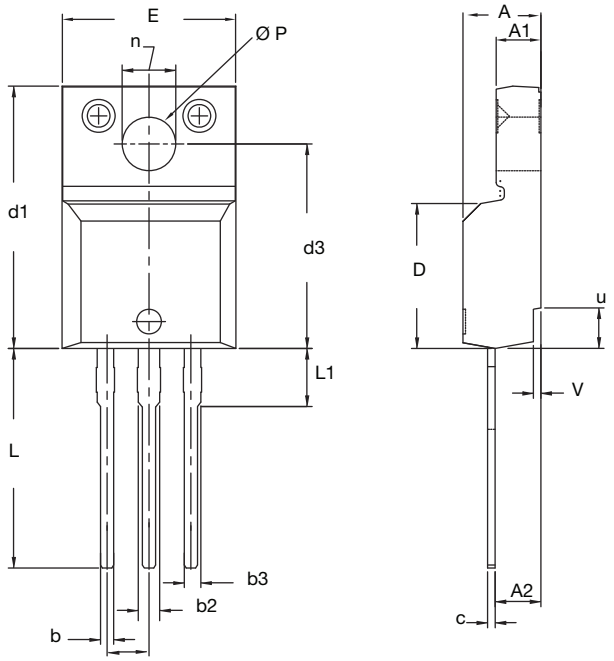


	MILLIMETERS		
DIM.	**MIN.**	**NOM.**	**MAX.**
A	4.60	4.70	4.80
b	0.70	0.80	0.91
b1	1.20	1.30	1.47
b2	1.10	1.20	1.30
C	0.45	0.50	0.63
D	15.80	15.87	15.97
e		2.54 BSC	
E	10.00	10.10	10.30
F	2.44	2.54	2.64
G	6.50	6.70	6.90
L	12.90	13.10	13.30
L1	3.13	3.23	3.33
Q	2.65	2.75	2.85
Q1	3.20	3.30	3.40
Ø R	3.08	3.18	3.28

Notes

1. To be used only for process drawing
2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1st character located at the 2nd row of the unit marking

OPTION 2: FACILITY CODE = Y

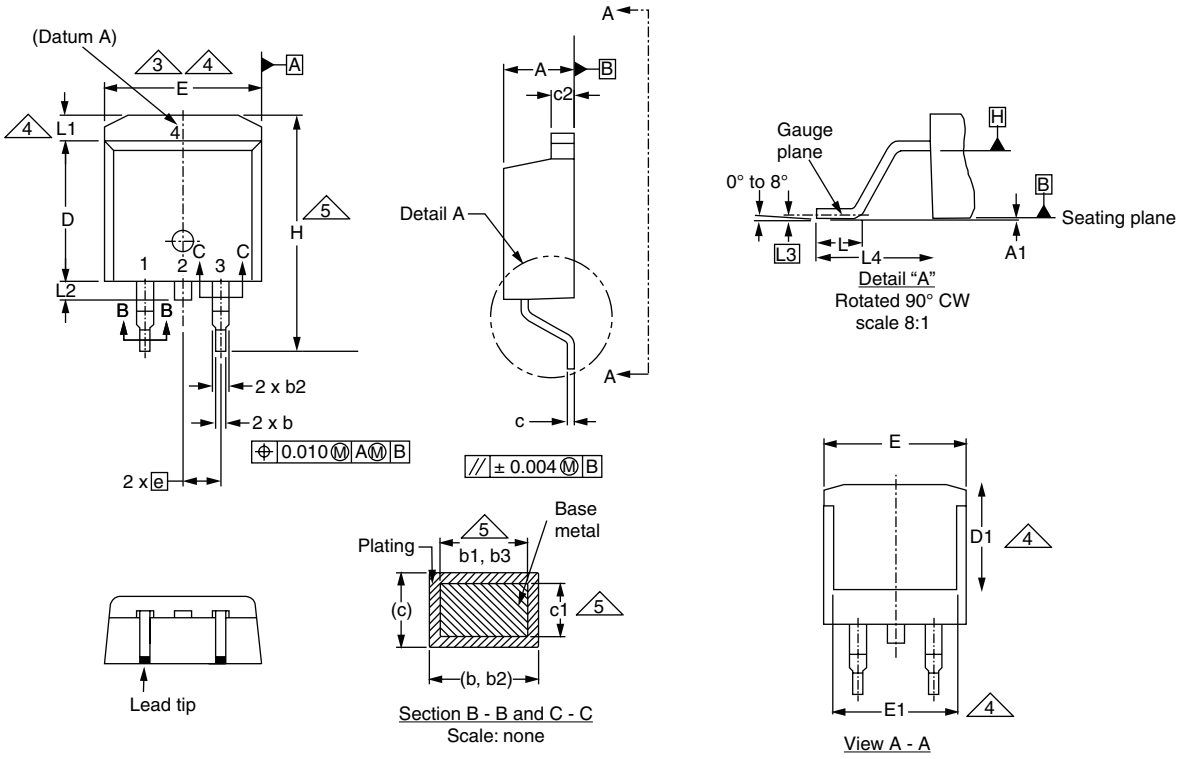


	MILLIMETERS		INCHES	
DIM.	**MIN.**	**MAX.**	**MIN.**	**MAX.**
A	4.570	4.830	0.180	0.190
A1	2.570	2.830	0.101	0.111
A2	2.510	2.850	0.099	0.112
b	0.622	0.890	0.024	0.035
b2	1.229	1.400	0.048	0.055
b3	1.229	1.400	0.048	0.055
c	0.440	0.629	0.017	0.025
D	8.650	9.800	0.341	0.386
d1	15.88	16.120	0.622	0.635
d3	12.300	12.920	0.484	0.509
E	10.360	10.630	0.408	0.419
e	2.54 BSC		0.100 BSC	
L	13.200	13.730	0.520	0.541
L1	3.100	3.500	0.122	0.138
n	6.050	6.150	0.238	0.242
Ø P	3.050	3.450	0.120	0.136
u	2.400	2.500	0.094	0.098
V	0.400	0.500	0.016	0.020
ECN: E19-0180-Rev. D, 08-Apr-2019 DWG: 5972				

Notes

1. To be used only for process drawing
2. These dimensions apply to all TO-220 FULLPAK leadframe versions 3 leads
3. All critical dimensions should C meet $C_{pk} > 1.33$
4. All dimensions include burrs and plating thickness
5. No chipping or package damage
6. Facility code will be the 1st character located at the 2nd row of the unit marking

TO-263AB (HIGH VOLTAGE)



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

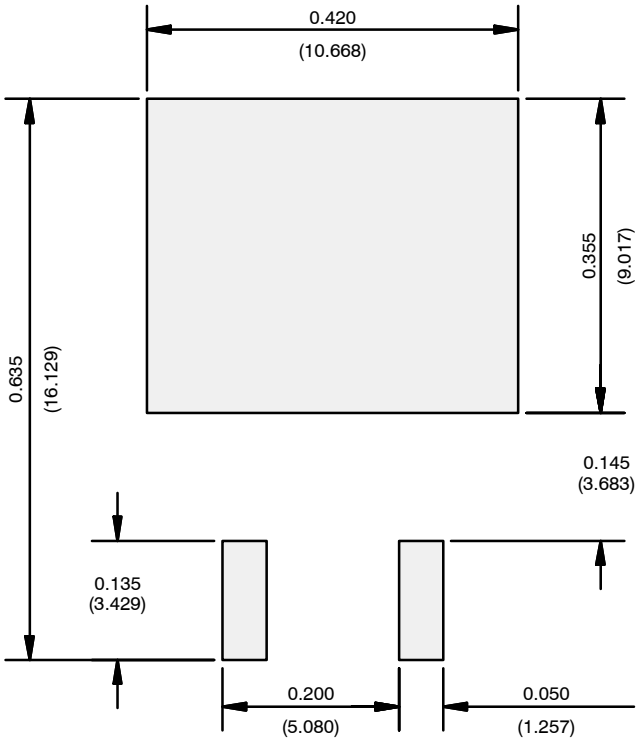
	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08
DWG: 5970

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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